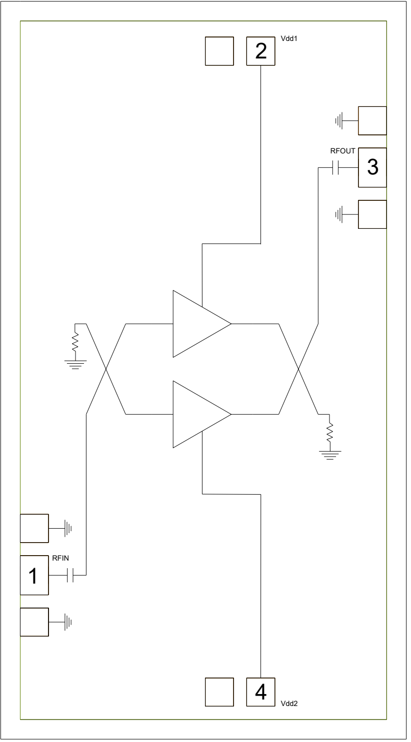
CMD200

9-13 GHz Balanced Driver Amplifier

Features

- ► Low noise performance
- ► High linearity
- ► Low current consumption
- ► Excellent return losses
- ► Small die size

Functional Block Diagram



Description

The CMD200 is a GaAs MMIC driver amplifier ideally suited for military, space and communications systems where small size and high linearity are needed. At 11 GHz the device delivers 15.5 dB of gain with a corresponding output 1 dB compression point of +15.5 dBm and noise figure of 3.25 dB. The CMD200 is a 50 ohm matched design which eliminates the need for external DC blocks and RF port matching. The CMD200 offers full passivation for increased reliability and moisture protection.

Electrical Performance - V_{dd1} = V_{dd2} = 5.0 V, T_A = 25 ^oC, F = 11 GHz

Parameter	Min	Typ	Max	Units
Frequency Range		9 - 13		GHz
Gain		15.5		dB
Noise Figure		3.25		dB
Input Return Loss		15		dB
Output Return Loss		19		dB
Output P1dB		15.5		dBm
Supply Current (I_{dd1} + I_{dd2})		38		mA

ver 1.3 0218

Specifications

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, Vdd1, Vdd2	6.0 V
RF Input Power	+20 dBm
Channel Temperature, Tch	150 °C
Power Dissipation, Pdiss	521 mW
Thermal Resistance	124.7 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
Vdd1, Vdd2	2.0	5.0	6.0	V
Idd1		19		mA
Idd2		19		mA

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

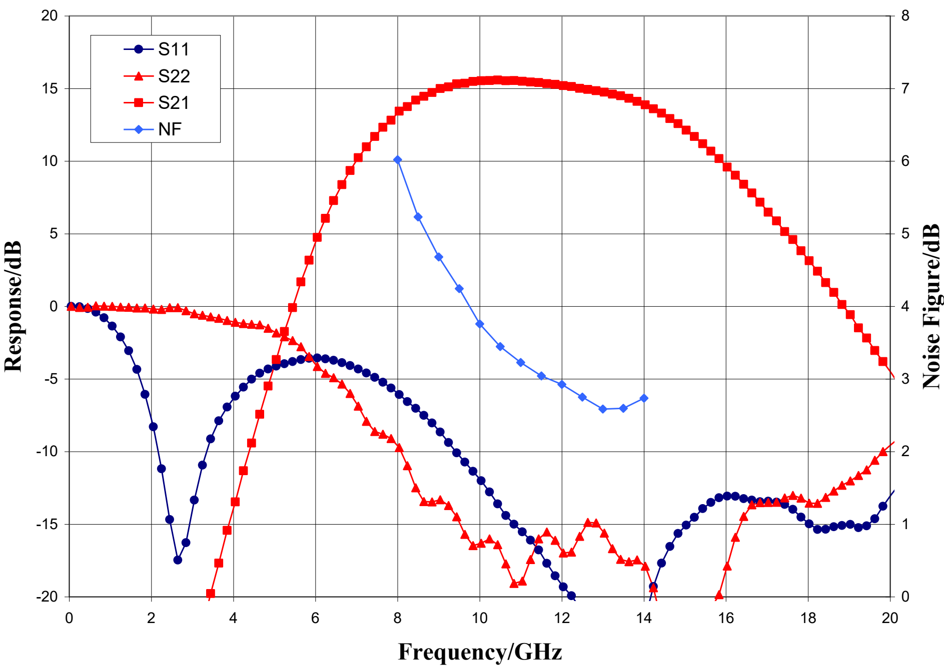
Electrical Specifications, $V_{dd1} = V_{dd2} = 5.0$ V, $T_A = 25$ °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range		9 - 11			11 - 13		GHz
Gain	12.5	15.5	18.5	12	15	18.5	dB
Noise Figure		3.75			3		dB
Input Return Loss		12			19		dB
Output Return Loss		16			16		dB
Output P1dB	12	15		13	16		dBm
Output IP3		21			20.5		dBm
Supply Current ($I_{dd1} + I_{dd2}$)	26	38	50	26	38	50	mA
Gain Temperature Coefficient		0.017			0.017		dB/°C
Noise Figure Temperature Coefficient		0.012			0.012		dB/°C

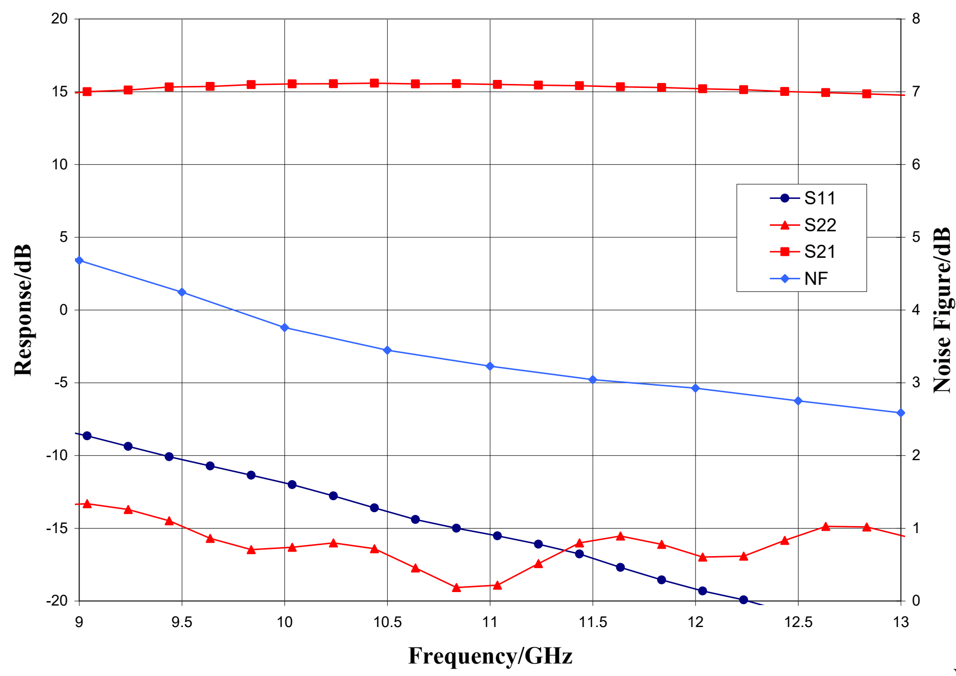
Custom MMIC
300 Apollo Drive Chelmsford, MA 01824 Phone (978) 467-4290 Fax (978) 467-4294
Visit us online at www.custommmic.com

Typical Performance

Broadband Performance, $V_{dd1} = V_{dd2} = 5.0$ V, $I_{dd1} = I_{dd2} = 19$ mA, $T_A = 25\ ^oC$



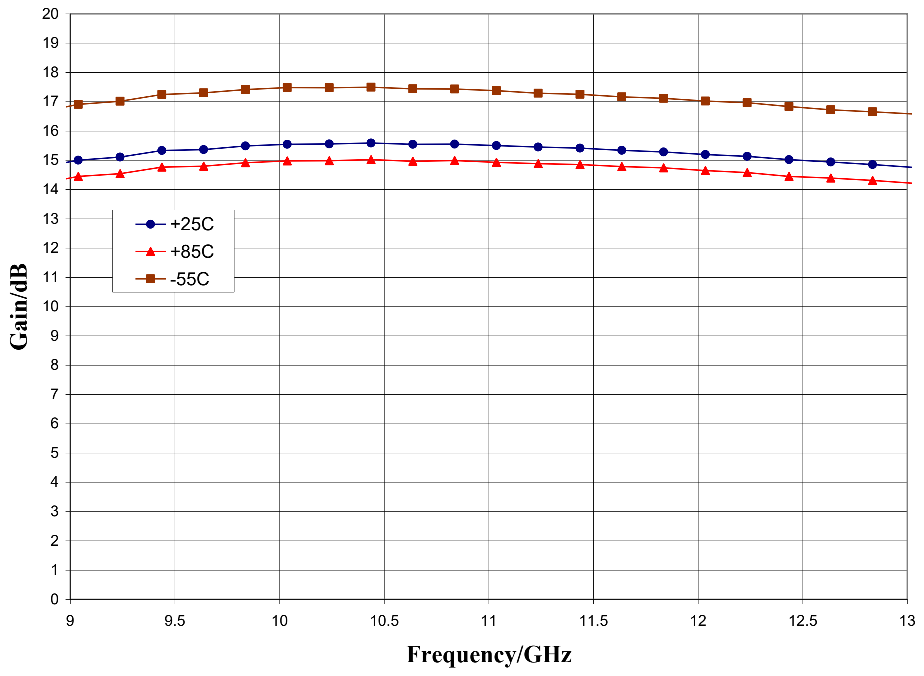
Narrow-band Performance, $V_{dd1} = V_{dd2} = 5.0$ V, $I_{dd1} = I_{dd2} = 19$ mA, $T_A = 25\ ^oC$



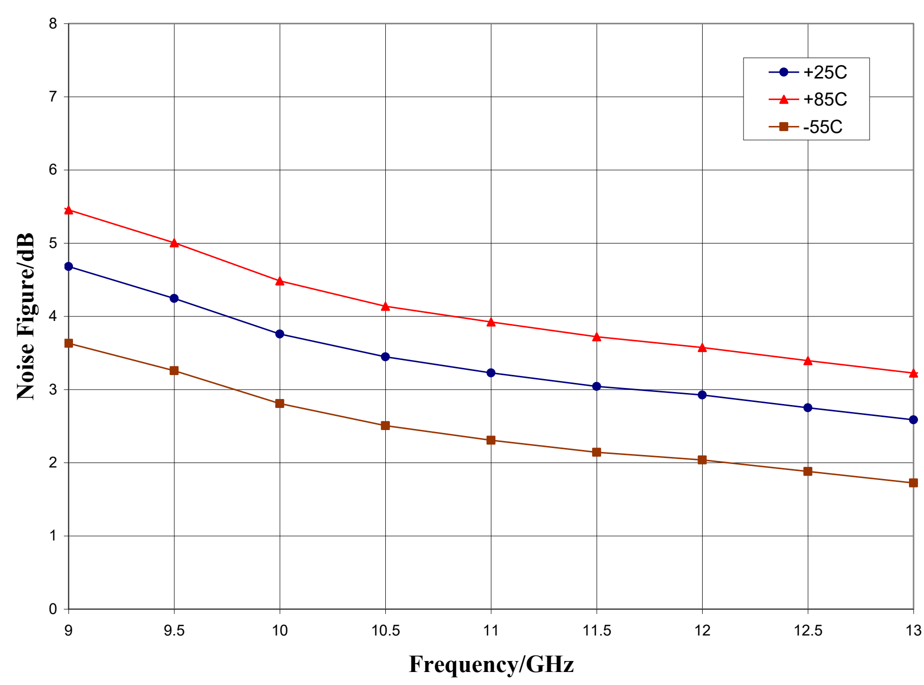
Custom MMIC
300 Apollo Drive Chelmsford, MA 01824 Phone (978) 467-4290 Fax (978) 467-4294
Visit us online at www.custommmic.com

Typical Performance

Gain vs. Temperature, $V_{dd1} = V_{dd2} = 5.0$ V



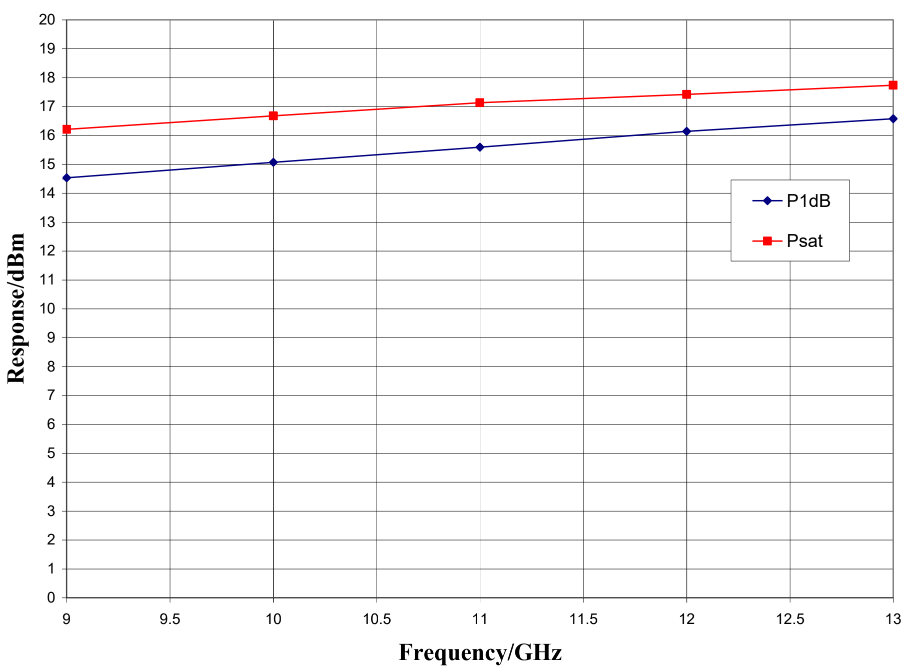
Noise Figure vs. Temperature, $V_{dd1} = V_{dd2} = 5.0$ V



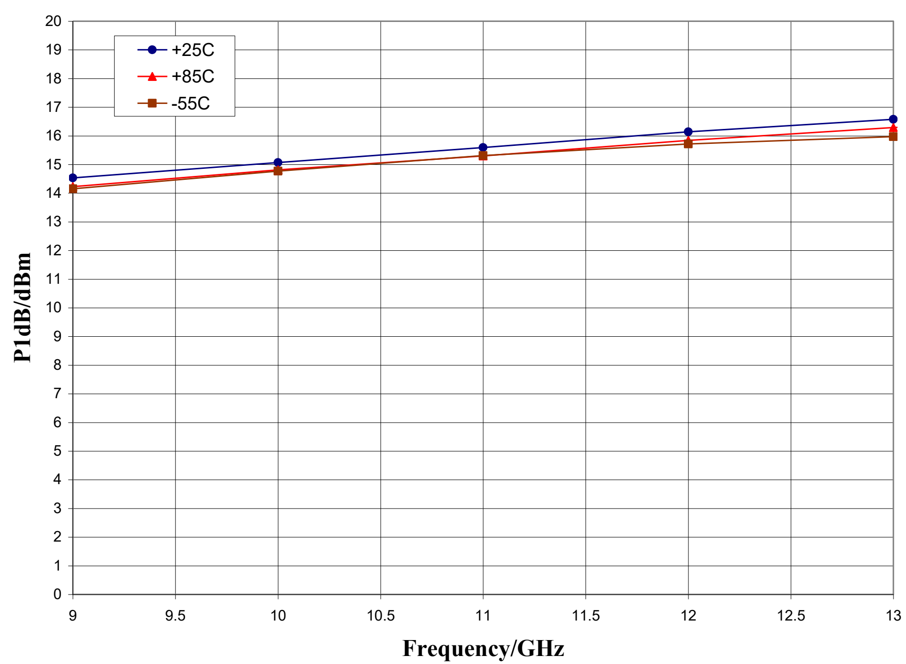
ver 1.3 0218

Typical Performance

Output Power, $V_{dd1} = V_{dd2} = 5.0$ V, $T_A = 25\ ^oC$



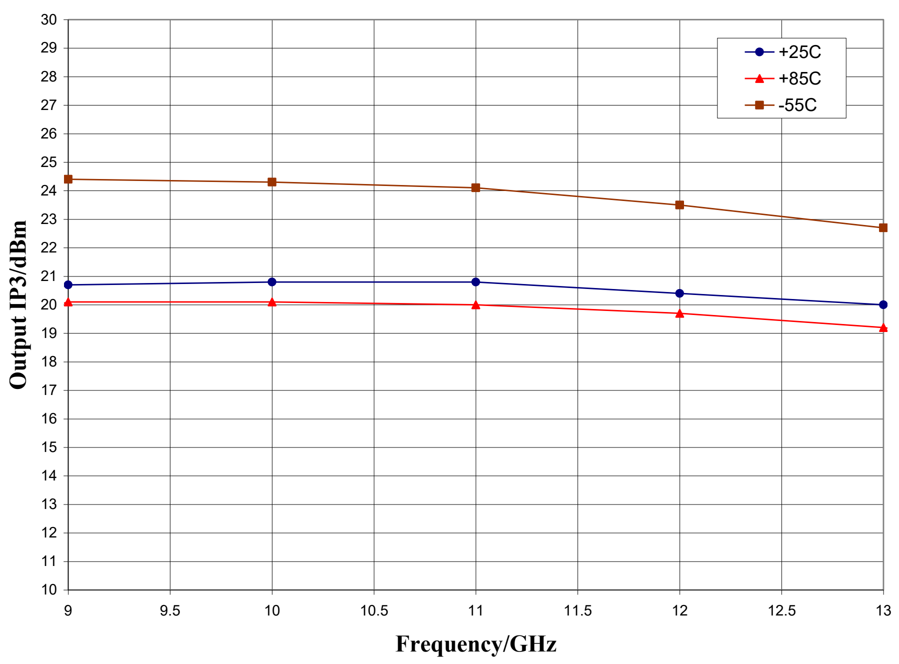
P1dB vs. Temperature, $V_{dd1} = V_{dd2} = 5.0$ V



Custom MMIC
300 Apollo Drive Chelmsford, MA 01824 Phone (978) 467-4290 Fax (978) 467-4294
Visit us online at www.custommmic.com

Typical Performance

Output IP3 vs. Temperature, $V_{dd1} = V_{dd2} = 5.0$ V



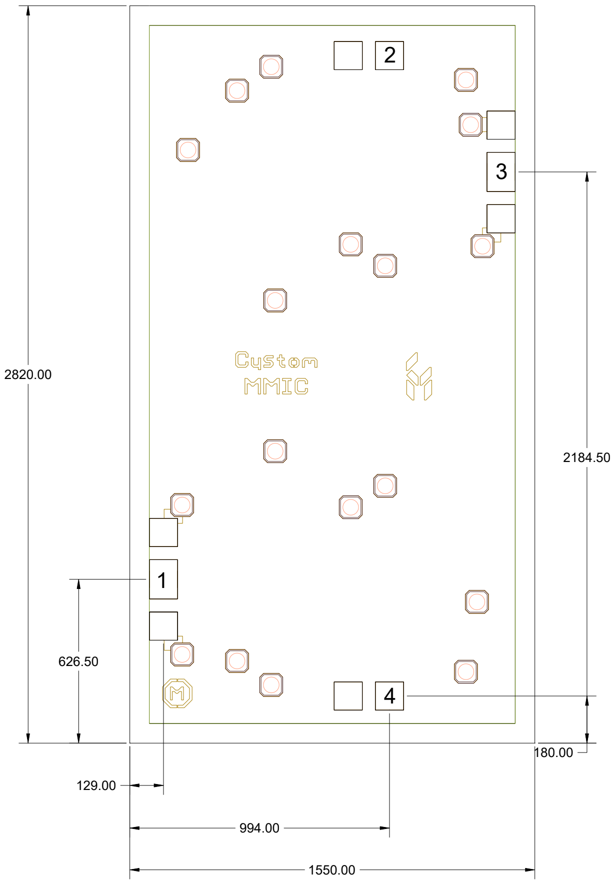
Custom MMIC
300 Apollo Drive Chelmsford, MA 01824 Phone (978) 467-4290 Fax (978) 467-4294
Visit us online at www.custommmic.com

CMD200

9-13 GHz Balanced Driver Amplifier

Mechanical Information

Die Outline (all dimensions in microns)



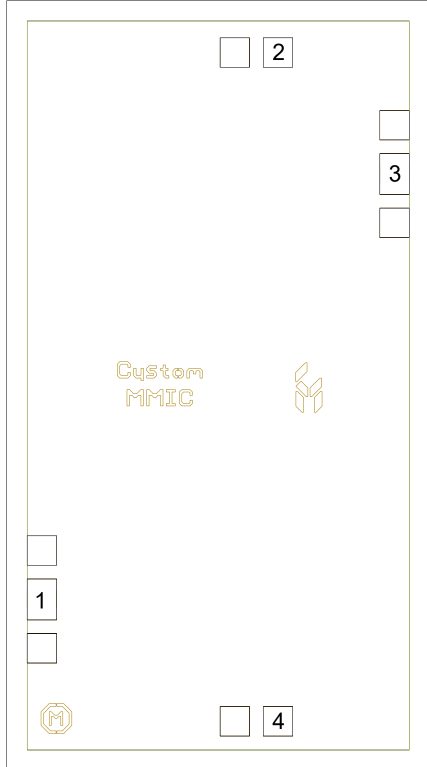
Notes:
1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads are 100 microns square
6. RF bond pads are 100 x 150 micron

ver 1.3 0218

Custom MMIC
300 Apollo Drive Chelmsford, MA 01824 Phone (978) 467-4290 Fax (978) 467-4294
Visit us online at www.custommmic.com

Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC blocked and 50 ohm matched	RF in
2, 4	Vdd1, Vdd2	Power supply voltage Decoupling and bypass caps required	Vdd
3	RF out	DC blocked and 50 ohm matched	RF out
Backside	Ground	Connect to RF / DC ground	GND

ver 1.3 0218

Applications Information

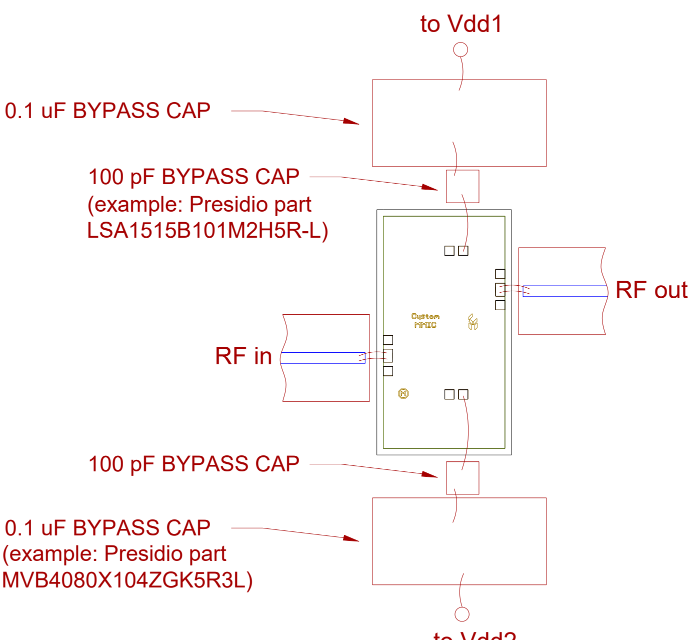
Assembly Guidelines

The backside of the CMD200 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85 um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

ver 1.3 0218

Applications Information

Biasing and Operation

The CMD200 is biased with a positive drain supply. Performance is optimized when the drain voltage is set to +5.0 V.

Turn ON procedure:

1.Apply drain voltage V_{dd1}, V_{dd2} and set to +5 V

Turn OFF procedure:

1.Turn off drain voltage V_{dd1}, V_{dd2}

RF power can be applied at any time.

Custom MMIC
300 Apollo Drive Chelmsford, MA 01824 Phone (978) 467-4290 Fax (978) 467-4294
Visit us online at www.custommmic.com